











SN74AHCT1G08

SCLS315Q -MARCH 1996-REVISED APRIL 2016

SN74AHCT1G08 Single 2-Input Positive-AND Gate

Features

- Operating Range: 4.5 V to 5.5 V
- Maximum t_{pd} of 7.1 ns at 5 V
- Low Power Consumption: Maximum I_{CC} of 10- μA
- ±8-mA Output Drive at 5 V
- Inputs Are TTL-Voltage Compatible
- Latch-Up Performance Exceeds 250 mA Per JESD 17

2 Applications

- TV, Set-Top Box, and Audio
- Wireless Infrastructure
- **Factory Automation and Control**
- PC and Notebooks
- **Building Automation**
- Grid Infrastructure
- Medical, Healthcare, and Fitness
- **Printers**
- **Test and Measurement**
- EPOS (Electronic Point of Sale)
- Telecom Infrastructure
- **Projectors**

3 Description

The SN74AHCT1G08 device is a single 2-input positive-AND gate. The device performs the Boolean function $Y = A \cdot B$ or $Y = \overline{A + B}$ in positive logic. Low I_{CC} current allows this device to be used in powersensitive or battery-powered applications.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74AHCT1G08DBVR	SOT-23 (5)	2.90 mm x 1.60 mm
SN74AHCT1G08DCKR	SC70 (5)	2.00 mm x 1.25 mm
SN74AHCT1G08DRLR	SOT (5)	1.60 mm x 1.20 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram





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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision P (May 2013) to Revision Q

Page

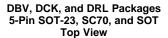
Added Applications section, Device Information table, Table of Contents, Pin Configuration and Functions section, Specifications section, ESD Ratings table, Thermal Information table, Typical Characteristics section, Detailed Description section, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section...... 1

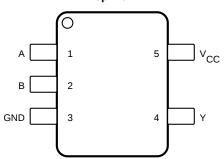
Changes from Revision O (June 2005) to Revision P

Page



5 Pin Configuration and Functions





Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
Α	1	I	Input A
В	2	ı	Input B
GND	3	_	Ground Pin
V_{CC}	5	_	Supply Pin
Υ	4	0	Output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted). (1)

			MIN	MAX	UNIT
Supply voltage		-0.5	7	V	
Input voltage ⁽²⁾				7	V
Output voltage (2)			-0.5	V _{CC} + 0.5	V
Input clamp current	V _I < 0			-20	mA
Output clamp current	V _O < 0 or V _O > V _{CC}			±20	mA
Continuous output current	$V_O = 0$ to V_{CC}			±25	mA
Continuous current through V _{CC} or GND				±50	mA
Maximum junction temperature, T _J				150	°C
Storage temperature, T _{stg}			-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

				VALUE	UNIT
.,		Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2500	V
V	(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

Product Folder Links: SN74AHCT1G08

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	٧
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_{I}	Input voltage	0	5.5	٧
V_{O}	Output voltage	0	V_{CC}	V
I _{OH}	High-level output current		-8	mA
I _{OL}	Low-level output current		8	mA
$\Delta t/\Delta v$	Input transition rise and fall rate		20	ns/V
T_A	Operating free-air temperature	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

6.4 Thermal Information

		SN74AHCT1G08					
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	DRL (SOT)	UNIT		
		5 PINS	5 PINS	5 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	226	277.5	242.9	°C/W		
R ₀ JC(top)	Junction-to-case (top) thermal resistance	165	92.9	77.5	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	59.1	64.2	77.5	°C/W		
ΨЈТ	Junction-to-top characterization parameter	45.5	1.9	9.6	°C/W		
ΨЈВ	Junction-to-board characterization parameter	58.3	63.5	77.3	°C/W		

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDIT	IONS	MIN	TYP	MAX	UNIT	
		$I_{OH} = -50 \mu A, V_{CC} = 4.5 V$		4.4	4.5			
.,	High-level output	$V_{OH} = -30 \ \mu \text{A}, \ V_{CC} = 4.3 \ \text{V}$	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$	4.4			V	
V _{OH}	voltage	1 0 m	$T_A = 25^{\circ}C$	3.94			V	
		$I_{OH} = -8 \text{ mA}, V_{CC} = 4.5 \text{ V}$	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$	3.8				
		$I_{OL} = 50 \mu A, V_{CC} = 4.5 V$				0.1		
V_{OL}	Low-level output voltage	Low-level output	· · · · · · · · · · · · · · · · · · ·	T _A = 25°C			0.36	V
		1 _{OL} = 6 IIIA, V _{CC} = 4.5 V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			0.44		
	lanut aurrant	$V_I = 5.5 \text{ V or GND},$	$T_A = 25^{\circ}C$			±0.1		
I _I	Input current	$V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±1	μΑ	
	Cumply ourrant	$V_I = V_{CC}$ or GND, $I_O = 0$,	T _A = 25°C			1		
Icc	Supply current	V _{CC} = 5.5 V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			10	μΑ	
$\Delta I_{CC}^{(1)}$	Change in supply One input at 3.4 V, Other Inputs	T _A = 25°C			1.35	A		
ΔICC	current	at V_{CC} or GND, $V_{CC} = 5.5 \text{ V}$	$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$			1.5	mA	
C _I	Input capacitance	$V_I = V_{CC}$ or GND, $V_{CC} = 5 \text{ V}$			4	10	pF	

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

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6.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 2)

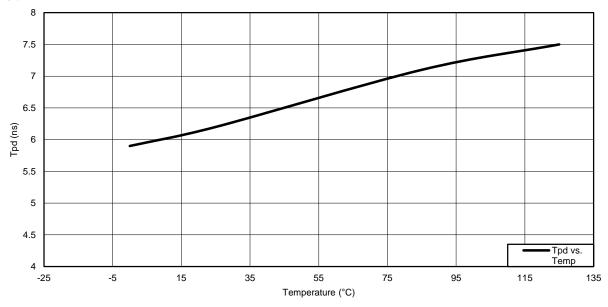
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
					T _A = 25°C		5	6.2	<u> </u>	
t _{PLH}	Propagation delay, low to high transition	A or B	Y	$C_{L} = 15 \text{ pF}$	$T_A = -40$ °C to 85°C	1		7.1	ns	
	iow to riight transition				$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$	1		7.5		
					$T_A = 25$ °C		5	6.2		
t _{PHL}	Propagation delay, high to low transition	A or B	Υ		$T_A = -40$ °C to 85°C	1		7.1	ns	
					$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$	1		7.5	1	
	Propagation delay, low to high transition A or B					$T_A = 25$ °C		5.5	7.9	
t _{PLH}		A or B	Y	C _L = 50 pF	Propagation delay, high to low transition	1		9	ns	
					$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$	1		10		
		ropagation delay,			T _A = 25°C		5.5	7.9		
t _{PHL}	Propagation delay, high to low transition		Υ	$C_{L} = 50 \text{ pF}$	$T_A = -40$ °C to 85°C	1		9	ns	
	nigh to low transition				$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	1		10		

6.7 Operating Characteristics

 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd} Power dissipation capacitance	No load, f = 1 MHz	18	рF

6.8 Typical Characteristics



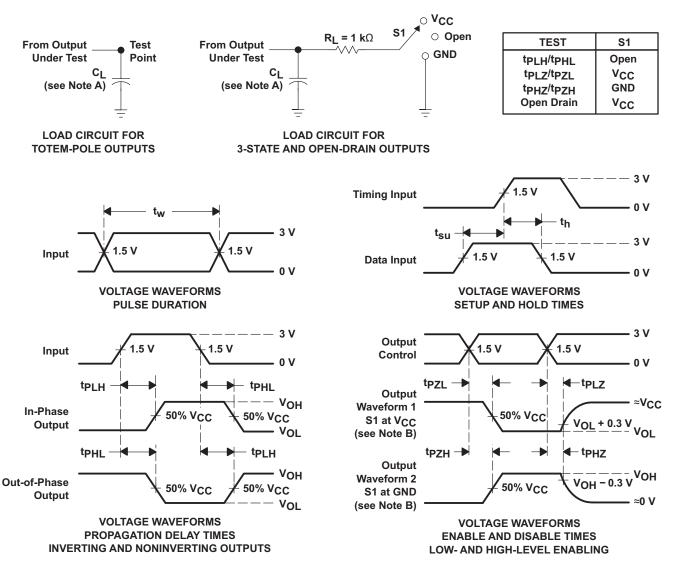
 $C_L = 15 pF$

Figure 1. T_{pd} vs Temperature

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7 Parameter Measurement Information



C_L includes probe and jig capacitance.

Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control

All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns.

The outputs are measured one at a time with one input transition per measurement.

All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms



8 Detailed Description

8.1 Overview

The SN74AHCT1G08 device is a single 2-input positive-AND gate. The device performs the Boolean AND function $(Y = A \cdot B \text{ or } Y = \overline{A + B})$ in positive logic. Low I_{CC} current allows this device to be used in powersensitive or battery-powered applications. Robust inputs allow the device to up-translate with a propagation delay of 20 ns.

8.2 Functional Block Diagram



Figure 3. Logic Diagram (Positive Logic)

8.3 Feature Description

The V_{CC} for the device is optimized at 5 V.

Up voltage translation from 3.3 V to 5 V is allowed. The inputs accept V_{IH} levels of 2 V.

Output ringing is minimized by slow edge rates.

Inputs are TTL-Voltage compatible.

8.4 Device Functional Modes

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Table 1 lists the functional modes of the SN74AHCT1G08.

Table 1. Function Table

INP	OUTPUT	
Α	В	Υ
Н	Н	Н
L	Х	L
X	L	L



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74AHCT1G08 device is a single AND gate, which is often used for many common functions like power sequencing or an *on* LED indicator. Because the device is configured to output LOW unless all inputs are HIGH, an LED tied to the output of the device will only turn HIGH when all systems connected are sending a HIGH, or *ready* signal.

9.2 Typical Application

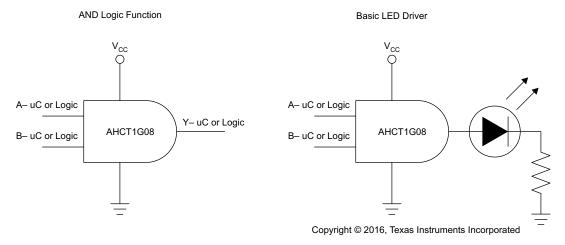


Figure 4. Typical Application Diagram

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads, so routing and load conditions must be considered to prevent ringing.

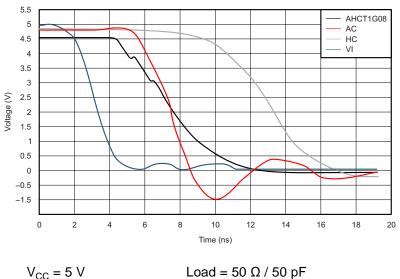
9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - For rise time and fall time specifications, see Δt/ΔV in Recommended Operating Conditions.
 - For specified high and low levels, see V_{IH} and V_{IL} in *Recommended Operating Conditions*.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended Output Conditions
 - Load currents must not exceed 25 mA per output and 50 mA total for the part.
 - Outputs must not be pulled above V_{CC}.



Typical Application (continued)

9.2.3 Application Curve



'

Figure 5. Typical Switching Characteristics

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Recommended Operating Conditions*.

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. TI recommends a 0.1- μ F capacitor for devices with a single supply; and a 0.01- μ F or 0.022- μ F capactor for each power pin if there are multiple V_{CC} pins. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Observe the following rules under all circumstances.

- All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating.
- The logic level that must be applied to any particular unused input depends on the function of the device.
 Generally they will be tied to GND or V_{CC}, whichever make more sense or is more convenient.

11.2 Layout Example



Figure 6. Layout Diagram



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following: Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.





4-Apr-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74AHCT1G08DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	B08G	Samples
74AHCT1G08DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	B08G	Samples
74AHCT1G08DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BE3, BEG, BEJ, BE L, BES)	Samples
74AHCT1G08DCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BE3, BEG, BEJ, BE L, BES)	Samples
74AHCT1G08DCKTG4	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BE3, BEG, BEL, BE S)	Samples
74AHCT1G08DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BEB, BES)	Samples
SN74AHCT1G08DBV3	ACTIVE	SOT-23	DBV	5	3000	Pb-Free (RoHS)	CU SNBI	Level-1-260C-UNLIM	-40 to 125	B08Y	Samples
SN74AHCT1G08DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(B083, B08G, B08J, B08L, B08S)	Samples
SN74AHCT1G08DBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(B083, B08G, B08J, B08L, B08S)	Samples
SN74AHCT1G08DCK3	ACTIVE	SC70	DCK	5	3000	Pb-Free (RoHS)	CU SNBI	Level-1-260C-UNLIM	-40 to 125	BEY	Samples
SN74AHCT1G08DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BE3, BEG, BEJ, BE L, BES)	Samples
SN74AHCT1G08DCKT	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(BE3, BEG, BEL, BE S)	Samples
SN74AHCT1G08DRLR	ACTIVE	SOT-5X3	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(BEB, BES)	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

4-Apr-2019

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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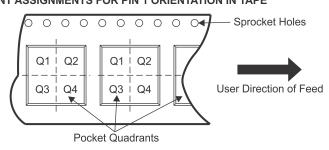
TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity AO

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74AHCT1G08DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHCT1G08DBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHCT1G08DBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHCT1G08DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AHCT1G08DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AHCT1G08DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHCT1G08DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AHCT1G08DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74AHCT1G08DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHCT1G08DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AHCT1G08DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74AHCT1G08DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74AHCT1G08DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AHCT1G08DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHCT1G08DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHCT1G08DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHCT1G08DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DRL (R-PDSO-N5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs.

 Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
- D. JEDEC package registration is pending.



DRL (R-PDSO-N5)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over—print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



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